

## Low voltage fast-switching PNP power transistor

### Features

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed
- Miniature SOT-23 plastic package for surface mounting circuits

### Applications

- LED
- Battery charger
- Motor and relay driver
- Voltage regulation

### Description

The 2STR2215 is a PNP transistor manufactured using new “PB-HCD” (Power Bipolar High Current Density) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage. The complementary NPN is the 2STR1215.

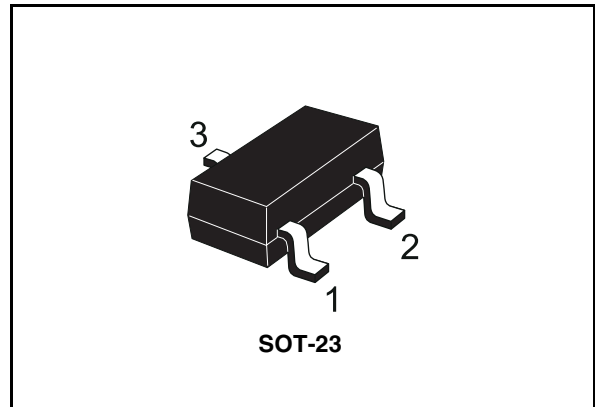


Figure 1. Internal schematic diagram

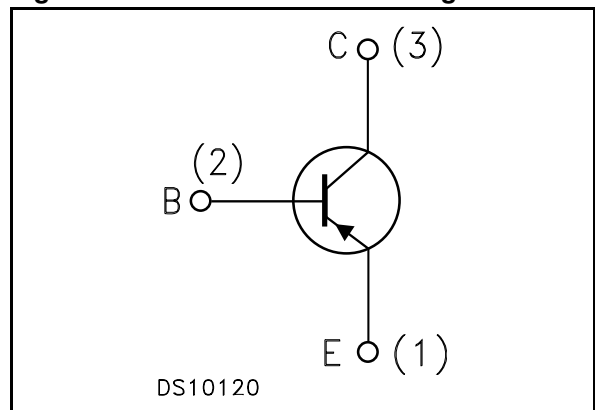


Table 1. Device summary

Order code	Marking	Package	Packaging
2STR2215	215	SOT-23	Tape and reel

## Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
2.1	Electrical characteristics (curves) .....	5
2.2	Test circuit .....	6
<b>3</b>	<b>Package mechanical data</b> .....	<b>7</b>
<b>4</b>	<b>Revision history</b> .....	<b>9</b>

# 1 Electrical ratings

**Table 2. Absolute maximum rating**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-base voltage ( $I_E = 0$ )	-15	V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	-15	V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ )	-5	V
$I_C$	Collector current	-1.5	A
$I_{CM}$	Collector peak current ( $t_P < 5$ ms)	-3	A
$P_{tot}$	Total dissipation at $T_{amb} = 25$ °C	0.5	W
$T_{stg}$	Storage temperature	-65 to 150	°C
$T_J$	Max. operating junction temperature	150	°C

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb max	250	°C/W

(1) Device mounted on PCB area of 1cm<sup>2</sup>

## 2 Electrical characteristics

( $T_{\text{case}} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)

**Table 4. Electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{\text{CBO}}$	Collector cut-off current ( $I_{\text{E}} = 0$ )	$V_{\text{CB}} = -15\text{ V}$			-0.1	$\mu\text{A}$
$I_{\text{EBO}}$	Emitter cut-off current ( $I_{\text{C}} = 0$ )	$V_{\text{EB}} = -4\text{ V}$			-0.1	$\mu\text{A}$
$V_{(\text{BR})\text{CBO}}$	Collector-base breakdown voltage ( $I_{\text{E}} = 0$ )	$I_{\text{C}} = -100\text{ }\mu\text{A}$	-15			V
$V_{(\text{BR})\text{CEO}}^{(1)}$	Collector-emitter breakdown voltage ( $I_{\text{B}} = 0$ )	$I_{\text{C}} = -10\text{ mA}$	-15			V
$V_{(\text{BR})\text{EBO}}$	Emitter-base breakdown voltage ( $I_{\text{C}} = 0$ )	$I_{\text{E}} = -100\text{ }\mu\text{A}$	-5			V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = -100\text{ mA}$ $I_{\text{B}} = -1\text{ mA}$			-0.15	V
		$I_{\text{C}} = -1\text{ A}$ $I_{\text{B}} = -100\text{ mA}$		-0.25	-0.50	V
		$I_{\text{C}} = -2\text{ A}$ $I_{\text{B}} = -200\text{ mA}$		-0.40	-0.85	V
$V_{\text{BE(sat)}}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = -1\text{ A}$ $I_{\text{B}} = -100\text{ mA}$		-0.90	-1.25	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_{\text{C}} = -50\text{ mA}$ $V_{\text{CE}} = -2\text{ V}$	200	280	560	
		$I_{\text{C}} = -500\text{ mA}$ $V_{\text{CE}} = -2\text{ V}$	200			
		$I_{\text{C}} = -1\text{ A}$ $V_{\text{CE}} = -2\text{ V}$	130			
		$I_{\text{C}} = -2\text{ A}$ $V_{\text{CE}} = -2\text{ V}$	80			
$C_{\text{CBO}}$	Collector-base capacitance ( $I_{\text{E}} = 0$ )	$V_{\text{CB}} = -10\text{ V}$ $f = 1\text{ MHz}$		20		pF
$t_{\text{on}}$ $t_{\text{off}}$	Resistive load Turn-on time	$I_{\text{C}} = -1.5\text{ A}$ $V_{\text{CC}} = -10\text{ V}$		60		ns
	Turn-off time	$I_{\text{B1}} = -I_{\text{B2}} = -150\text{ mA}$		220		ns

1. Pulsed duration = 300  $\mu\text{s}$ , duty cycle  $\leq 1.5\%$

# 2.1 Electrical characteristics (curves)

Figure 2. DC current gain

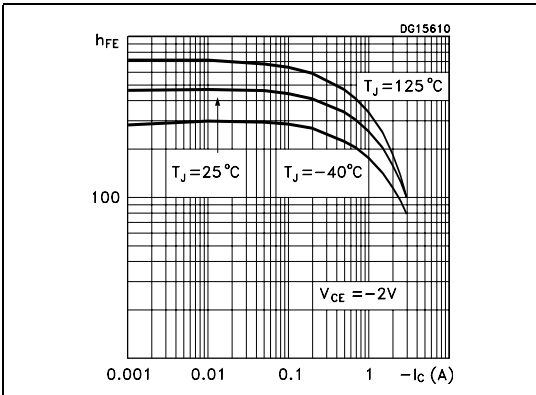


Figure 3. Collector-emitter saturation voltage

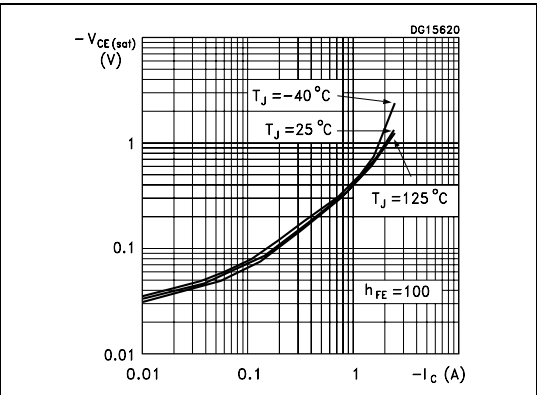


Figure 4. Base-emitter saturation voltage

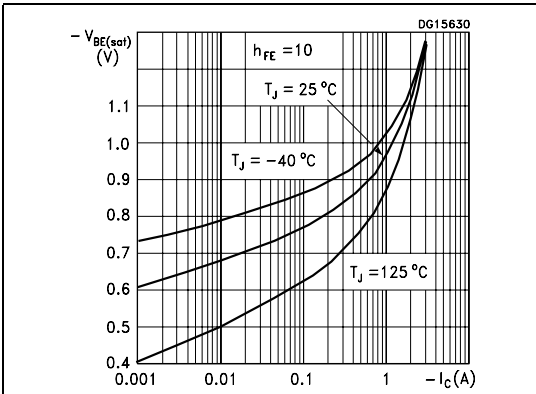


Figure 5. Resistive load switching time

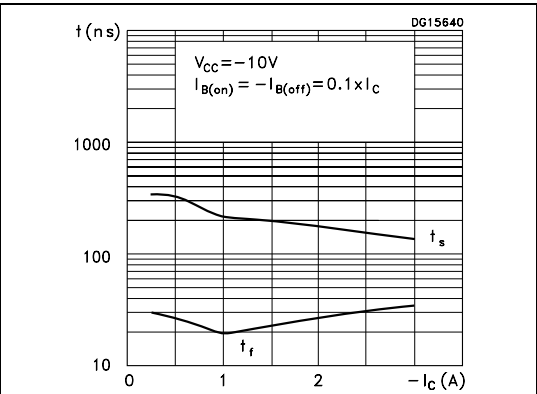


Figure 6. Resistive load switching time

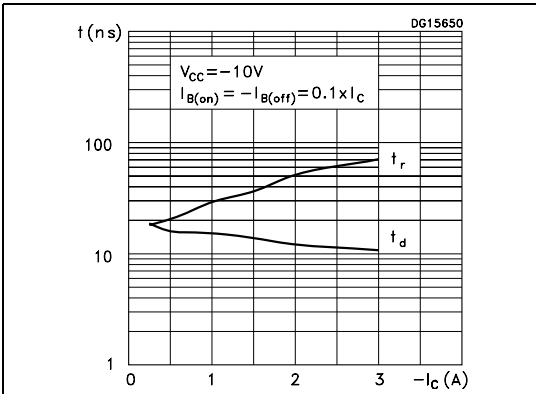
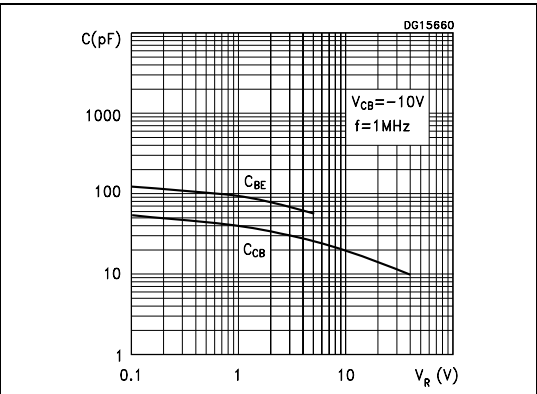
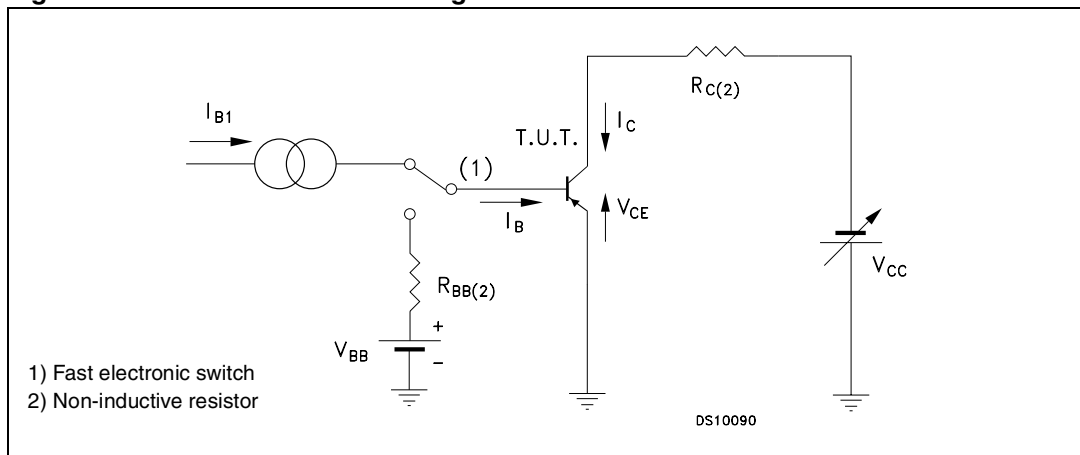


Figure 7. Capacitance



## 2.2 Test circuit

Figure 8. Resistive load switching test circuit

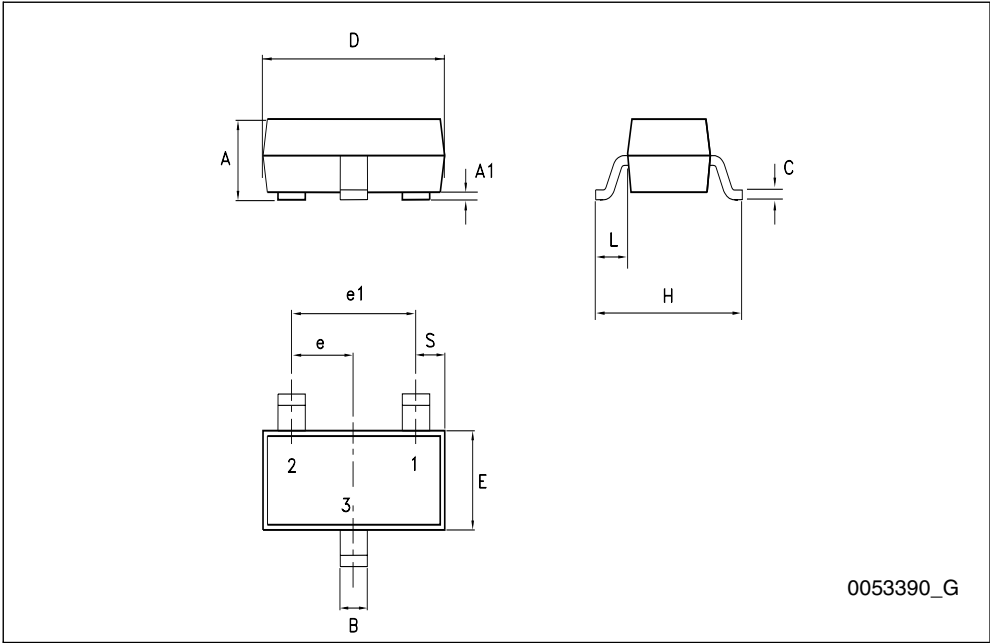


### 3      **Package mechanical data**

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

SOT-23 mechanical data

DIM.	mm.		
	min.	typ	max.
A	0.89		1.4
A1	0		0.1
B	0.3		0.51
C	0.085		0.18
D	2.75		3.04
e	0.85		1.05
e1	1.7		2.1
E	1.2		1.6
H	2.1		2.75
L		0.6	
S	0.35		0.65





## 4 Revision history

**Table 5. Document revision history**

Date	Revision	Changes
09-Feb-2006	1	Initial release.
20-Jul-2006	2	New template.
08-Sep-2008	3	Updated the SOT-23 mechanical data.

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